# **TOSHIBA**

RF Power Amplifier Module

# **S-AU81**

# Power Amplifier Modules for Domestic cdmaOne

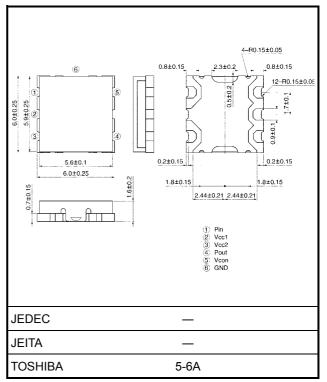
Unit: mm

- GaAs HBT Micro PA (on-chip bias circuit and matching circuit)
- Output power: Po = 27.0dBmW (min)
- Gain:  $G_p = 28.0 dB \text{ (typ.)}$
- Total current:  $I_t$  (1) = 385 mA (typ.) (@ $P_{out}$  = 27.0dBmW)
- Low-voltage operation: Operation at VCC = 1.5 V is possible

 $I_t(2) = 97 \text{ mA (typ) } (@P_{out} = 14dBmW, V_{CC} = 1.5 \text{ V})$ 

 This device features an output control pin which can be switched between low-power and high-power settings.

 $I_t = 90 \text{ mA (typ.)}$  (@Pout = 14dBmW,  $V_{CC} = 2.70 \text{ V}$ )



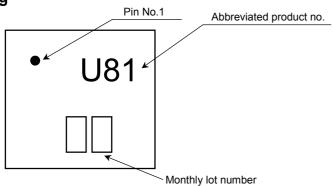
Weight: 0.0 g (typ.)

## Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Supply voltage 1	V <sub>CC1</sub>	5	V	
Supply voltage 2	V <sub>CC2</sub>	5	V	
Control voltage	V <sub>con</sub>	4	V	
Collector current	Icc	1	Α	
Power dissipation	P <sub>D</sub> (Note 1)	2	W	
Operating temperature	T <sub>op</sub>	-20 <b>~</b> +60	°C	
Storage temperature range	T <sub>stg</sub>	−30 <b>~</b> +125	°C	

Note 1:  $Ta = 25^{\circ}C$ 

### Marking





### **Electrical Characteristics (Tc = 25°C)**

Characteristic	s	Symbol	Test Condition		Min	Тур.	Max	Unit
Power gain (1)		G <sub>p</sub> (1)	V <sub>CC1</sub> , V <sub>CC 2</sub> = 3.6 V, V <sub>con</sub> = 2.85 V (Note 2),		25.0	28.0	_	dB
Control current		I <sub>con</sub>	$P_0$ = 27dBmW f = 887~925 MHz, $P_{in}$ = adjust, $Z_G$ = $Z_L$ = 50 Ω		_	3	5	mA
Total current (1)		I <sub>t</sub> (1)			_	385	_	mA
Adjacent-channel power ratio (1)		ACPR1 (1)	V <sub>con</sub> = 2.85 V (Note 2), P <sub>o</sub> = 27dBmW f = 887~925 MHz	900 kHz	_	-50	-45	dB
		ACPR2 (2)		1.98 MHz		-60	-56	dB
Power gain (2)		G <sub>p</sub> (2)	$V_{CC1}$ , $V_{CC\ 2}$ = 1.5 V, $V_{con}$ = 2.85 V (Note 2), $P_{o}$ = 14dBmW, f = 887~925 MHz, $P_{in}$ = adjust, $Z_{G}$ = $Z_{L}$ = 50 $\Omega$		21.0	24.0	1	dB
Total current (2)		I <sub>t</sub> (2)			_	97	_	mA
Adjacent-channel power		ACPR1 (2)	$V_{CC1}$ , $V_{CC 2} = 1.5 \text{ V}$ , $V_{con} = 2.85 \text{ V}$ (Note 2), $P_0 = 14 \text{dBmW}$ , $f = 887 \sim 925 \text{ MHz}$ , $Z_G = Z_L = 50 \Omega$ (Note 3)	900 kHz		-50	-45	dB
ratio (2)	ACPR2 (2)	1.98 MHz			-60	-56	dB	
Power gain (3)		G <sub>p</sub> (3)	$\begin{array}{l} V_{CC1},V_{CC\;2}=3.6\;V,V_{con}=2.85\;V\;(Note\;2),\\ P_{o}=27dBmW,f=887{\sim}925\;MHz,P_{in}=adjust,\\ Z_{G}=Z_{L}=50\;\Omega),T_{C}=-20{\sim}+60{\circ}C \end{array}$		24.0	27.0	_	dB
Adjacent-channel power ratio (3)		ACPR1 (3)	V <sub>CC1</sub> , V <sub>CC 2</sub> = 3.6 V, V <sub>con</sub> = 2.85 V (Note 2),	900 kHz	_	-48	-43	dB
		ACPR2 (3)	$P_0$ = 27dBmW, f = 887~925 MHz, $Z_G$ = $Z_L$ = 50 Ω, $T_C$ = -20~+60°C (Note 3)	1.98 MHz	_	-58	-55	dB
VSWRin		VSWRin	V <sub>CC1</sub> , V <sub>CC 2</sub> = 3.6 V, V <sub>con</sub> = 2.85 V (Note 3), P <sub>o</sub> = 27dBmW, f = 887~925 MHz, P <sub>in</sub> = adjust,			2	3	
Harmonics 2fo 3fo	HRM (1)	_			_	-30	dB	
	3fo	HRM (2)	$Z_G = Z_L = 50 \Omega$		_	_	-45	dB
Stability		SPR	$\begin{array}{l} V_{CC1},  V_{CC\;2} = 1.5\; \text{V},  2.5\; \text{V},  3.6\; \text{V},  4.2\; \text{V}, \\ V_{con} = 2.85\; \text{V} \; (\text{Note 3}),  P_0 \leqq 27 \text{dBmW}, \\ f = 887 \sim 925\; \text{MHz},  P_{in} = \text{adjust}, \\ Z_G = 50\; \Omega,  \text{VSWR} \; \text{LOAD} = 3:1 \; \text{all phase} \end{array}$		_	_	-60	dB
Receiving band noise NRB		NRB	$\begin{array}{l} V_{CC1},V_{CC\;2}=3.6\;V,V_{con}=2.85\;V\;(Note\;2),\\ P_0\leqq27dBmW,f=887{\sim}925\;MHz,P_{in}=adjust,\\ Z_G=Z_L=50\;\Omega \end{array}$		_	-135	_	dBmW/ Hz
Load mismatch			$\begin{array}{c} V_{CC1},V_{CC2}=1.5\;V^{-}4.2\;V,\\ V_{con}=2.85\;V\;(Note2),P_{o}\leqq27dBmW,\\ f=887^{-}925\;MHz,P_{in}=adjust,\\ Z_{G}=50\;\Omega,VSWR\;LOAD=3:1\;all\;phase \end{array}$		No degradation			_

Caution: This RF power amplifier is the electrostatic sensitive device. Please handle with caution.

Note 2:  $V_{con} = 2.85 \text{ V}$  is set to obtain Iidle  $\simeq 75 \text{ mA}$  when  $V_{CC1}$ ,  $V_{CC2} = 3.6 \text{ V}$ 

Note 3: ACPR

a) Pc (1.23 MHz) is average power measured for 1.23 MHz bandwidth with CDMA signal.

b) P (30 kHz) is average power measured for 30 kHz bandwidth with 900 kHz/1.98 MHz offset.

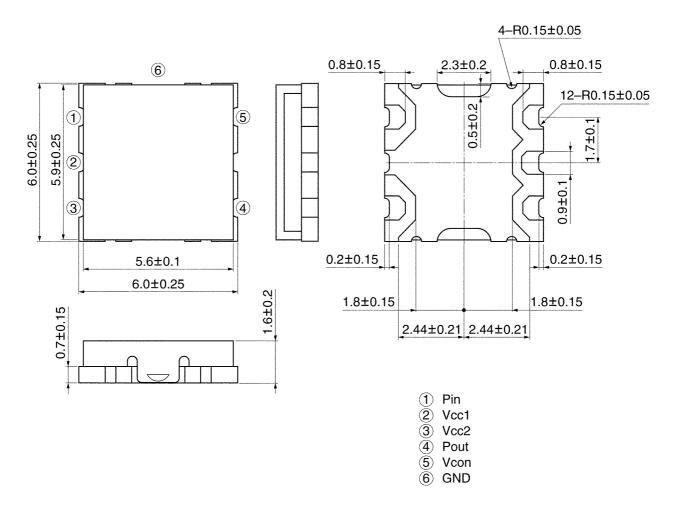
c) ACPR1 (or ACPR2) =  $P (30 \text{ kHz}) - P_c (1.23 \text{ MHz}) \text{ dB}$ 

Note 4: These electrical characteristics are measured using Toshiba recommended test board.

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## **Package Dimensions**

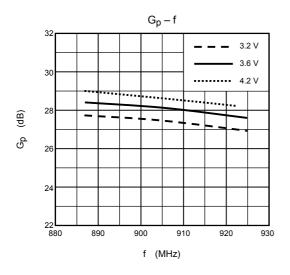
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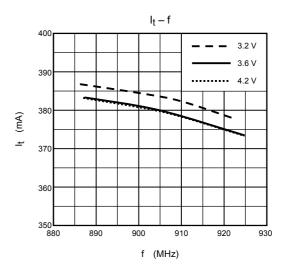


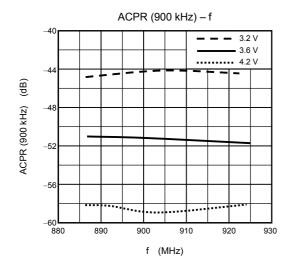
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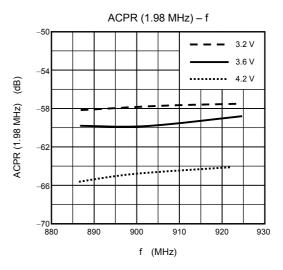
## **Typical Characteristic Curves**

(1) Frequency Characteristics  $P_0 = 27 dBmW, \, V_{con} = 2.85 \,\, V, \, V_{CC1}, \, V_{CC2} = 3.6 \,\, V$ 

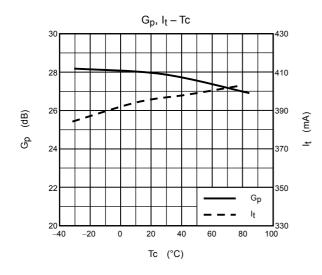


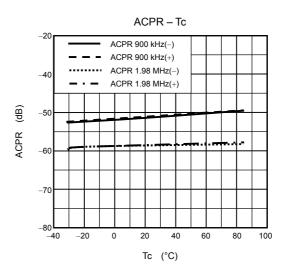






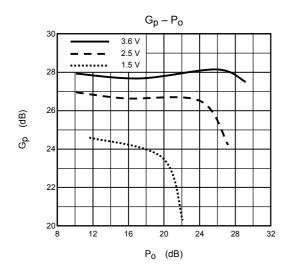
(2) Temperature Characteristics  $P_0 = 27 dBmW,\, V_{con} = 2.85 \,\, V,\, f = 906 \,\, MHz,\, V_{CC1},\, V_{CC2} = 3.6 \,\, V$ 

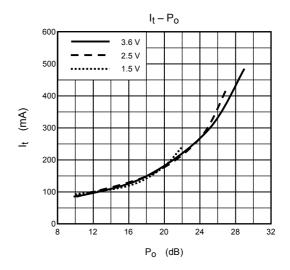


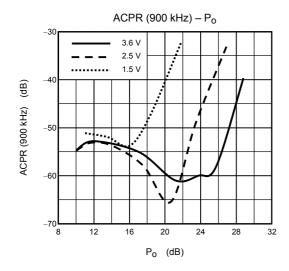


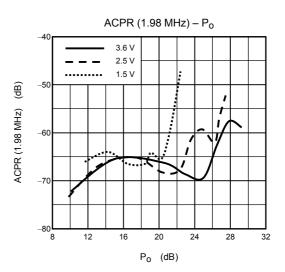
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(3) Power Supply Voltage  $\mbox{VCC Characteristics (f = 906 MHz, V}_{\mbox{con}} = 2.85 \mbox{ V)}$ 



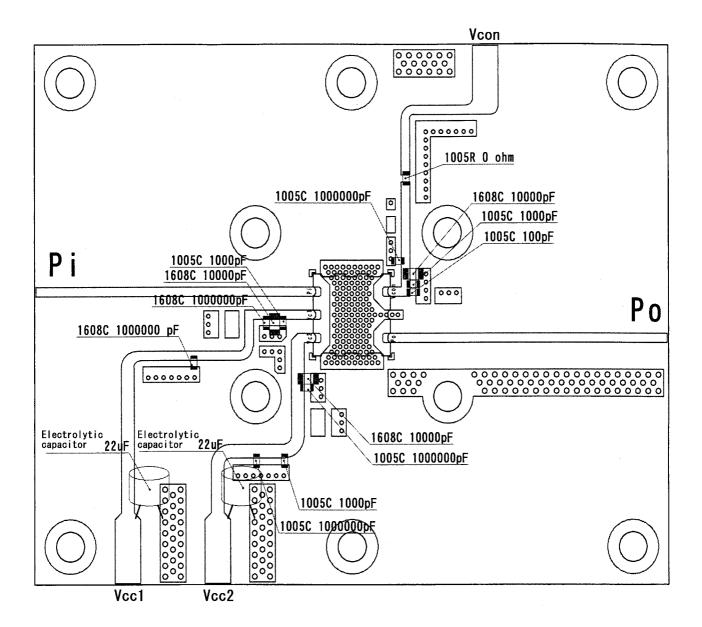






Note: These are only typical curves and devices are not necessarily guaranteed at these curves.

#### **Test Board**



Note for biasing procedure: Please follow this sequence when you measure a device bias sequence.

- a) V<sub>CC</sub>1, V<sub>CC</sub>2 On
- 0 V to Supply Voltage
- b) V<sub>con</sub> On
- adjust idle current
- c) RF on

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